PGD10N100

100V/65A N-Channel Advanced Power MOSFET

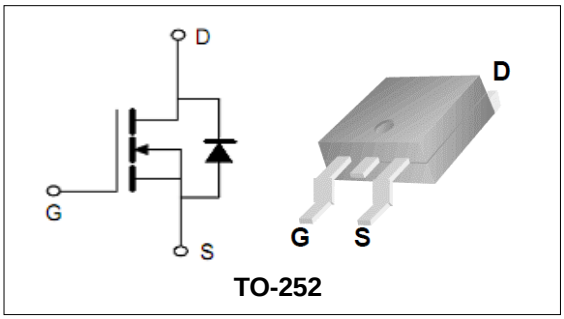
Features

- Fast switching
- Low RDS(on) & FOM
- Low Gate Charge

BVDSS	100	V
ID	65	A
RDSON@VGS=10V	7.8	mΩ
RDSON@VGS=4.5V	10.2	mΩ

Applications

- High Freuency Switching
- Synchronous Rectification



TO-252

Order Information

Product	Package	Marking	Reel Size	Reel	Carton
PGD10N100	TO-252	PGD10N100	13inch	2500PCS	50000PCS

Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)				
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage		100	V
V_{GS}	Gate-Source Voltage		±20	V
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	°C
I_S	Diode Continuous Forward Current	TC =25°C	65	A
Mounted on Large Heat Sink				
E_{AS}	Single Pulse Avalanche Energy (Note1)		102	mJ
I_{DM}	Pulse Drain Current Tested (Sillicon Limit) (Note2)	TC =25°C	240	A
I_D	Continuous Drain current	TC =25°C	65	A
P_D	Maximum Power Dissipation	TC =25°C	90	W
$R_{\theta Jc}$	Thermal Resistance Junction-to-Case (Note3)		1.39	°C/W

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Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
$V_{(BR)DSS}$	Drain- Source Breakdown Voltage	VGS=0V ID=250μA	100	--	--	V
I_{DSS}	Zero Gate Voltage Drain current	VDS=100V,VGS=0V	--	--	1	μA
I_{GSS}	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	VDS=VGS,ID=250μA	1	2	2.5	V
$R_{DS(ON)}$	Drain-Source On-State Resistance (Note4)	VGS=10V, ID=30A	--	7.8	9.2	mΩ
		VGS=4.5V, ID=15A	--	10.2	13.5	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated) (Note5)						
C_{iss}	Input Capacitance	VDS=50V, VGS=0V, F=1MHz	--	2140	--	pF
C_{oss}	Output Capacitance		--	495	--	pF
C_{rss}	Reverse Transfer Capacitance		--	36	--	pF
Q_g	Total Gate Charge	VDS=50V, ID=30A, VGS=10V	--	38	--	nC
Q_{gs}	Gate-Source Charge		--	6.7	--	nC
Q_{gd}	Gate-Drain Charge		--	5.6	--	nC
Switching Characteristics (Note5)						
$t_{d(on)}$	Turn-on Delay Time	VDS=50V, ID=25A, RG=6Ω, VGS=10V	--	13	--	nS
t_r	Turn-on Rise Time		--	39	--	nS
$t_{d(off)}$	Turn-off Delay Time		--	42	--	nS
t_f	Turn-off Fall Time		--	102	--	nS
Source- Drain Diode Characteristics@ TJ = 25°C (unless otherwise stated)						
V_{SD}	Forward on voltage	IS=20A,VGS=0V	--	--	1.2	V

Note:

1. Limited by TJmax, starting TJ = 25° C, RG = 25Ω, VD =30V, VGS =10V. Part not recommended for use above this value.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. Surface Mounted on FR4 Board, t ≤ 10 sec.
4. Pulse Test: pulse width ≤ 300 us, duty cycle ≤ 2%.
5. Guranteed by design, not subject to production testing.

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Typical Characteristics

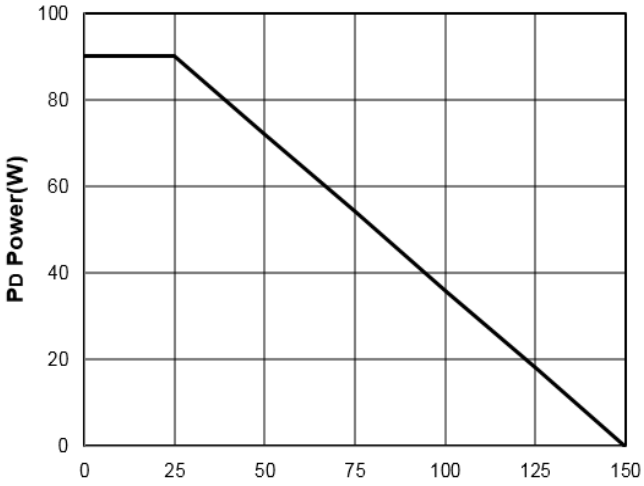

Figure1：T_J Junction Temperature（°C）

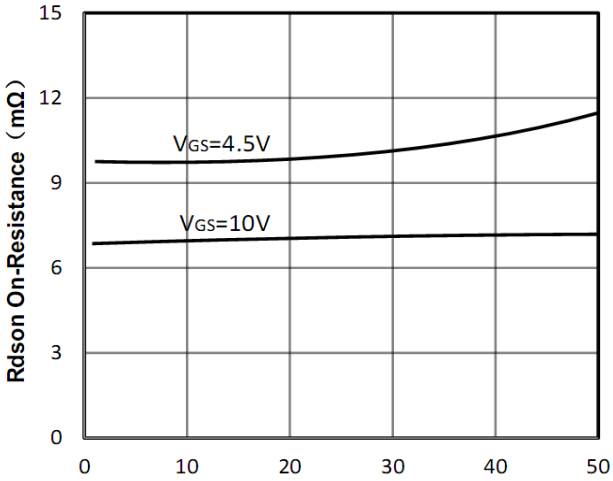

Figure2：I_D Drain Current（A）

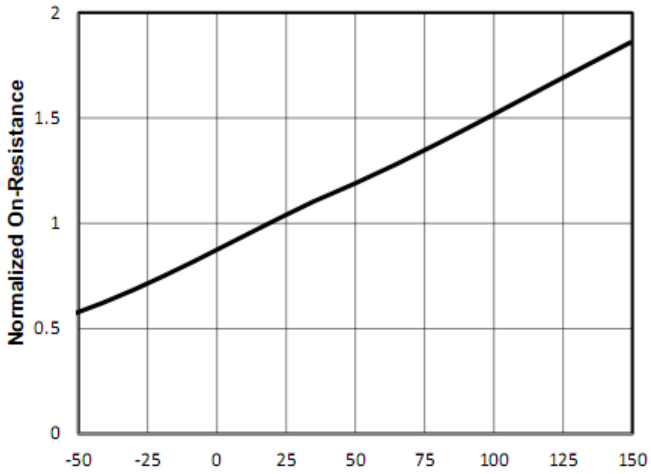

Figure3：T_J Junction Temperature（°C）

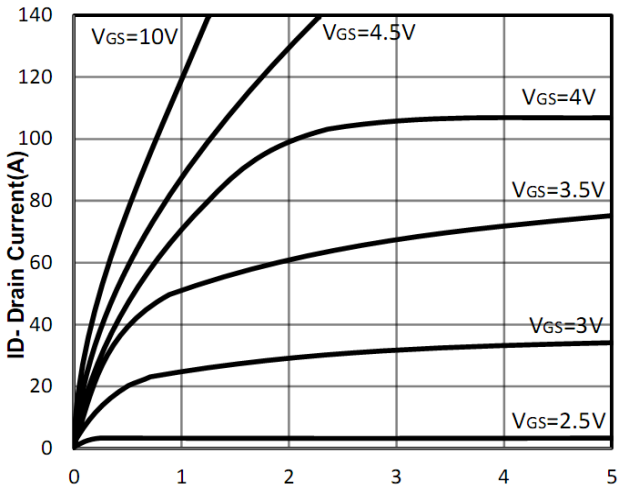

Figure4：V_{DS} Drain-Source Voltage（V）

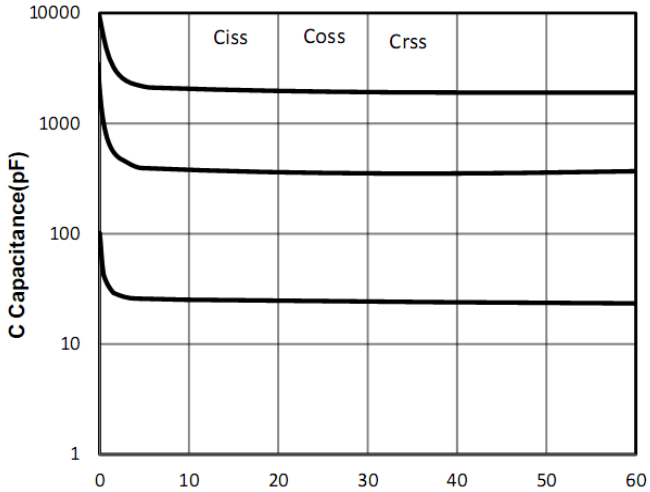

Figure5：V_{DS} Draun-Source Voltage（V）

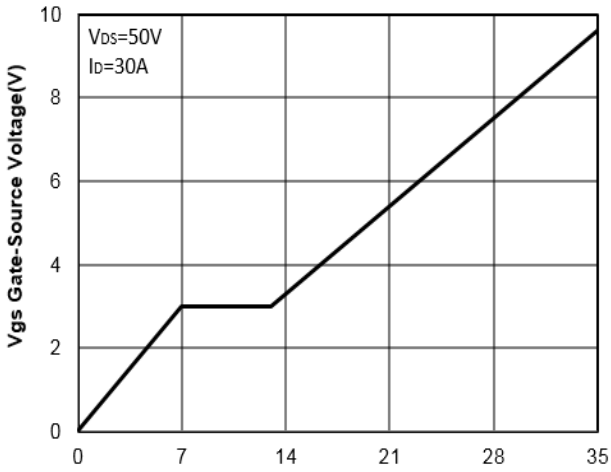

Figure6：Qg Gate Charge（nC）

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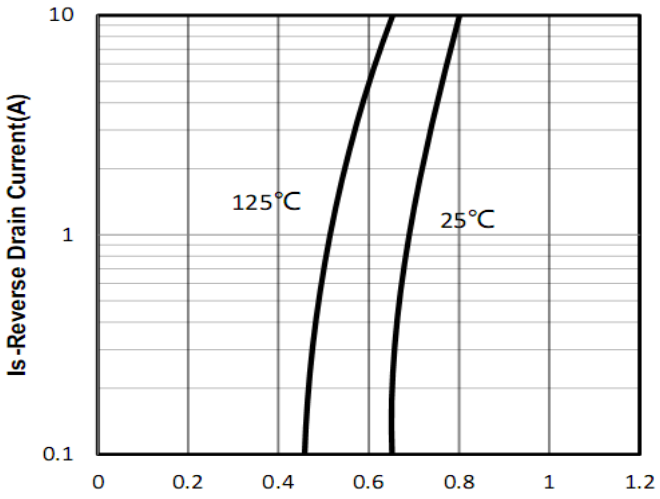

Figure7：Vsd Source-Drain Voltage（V）

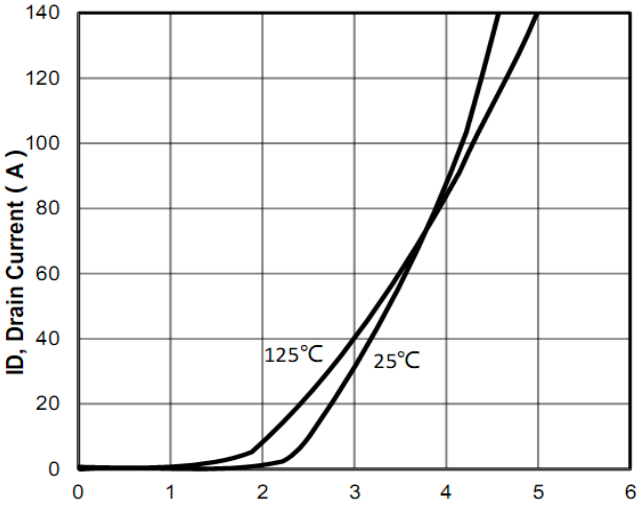

Figure8：Vgs Gate-Source Voltage（V）

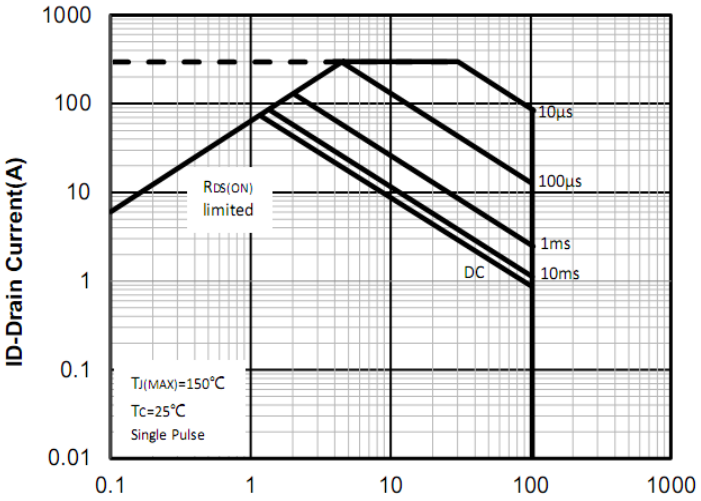

Figure9：Vds Drain -Source Voltage（V）

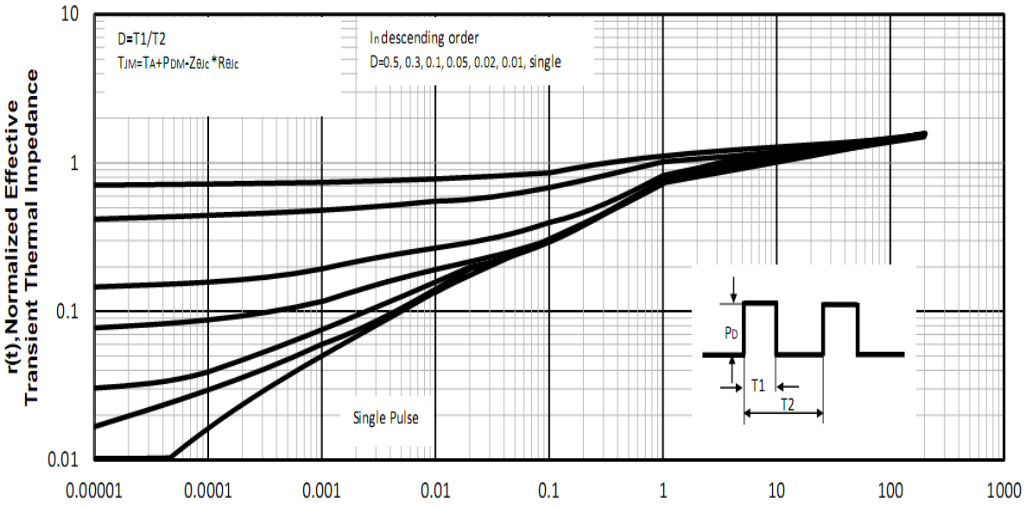

Figure10：Square Wave Pulse Duration（sec）

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Test Circuit and Waveform:

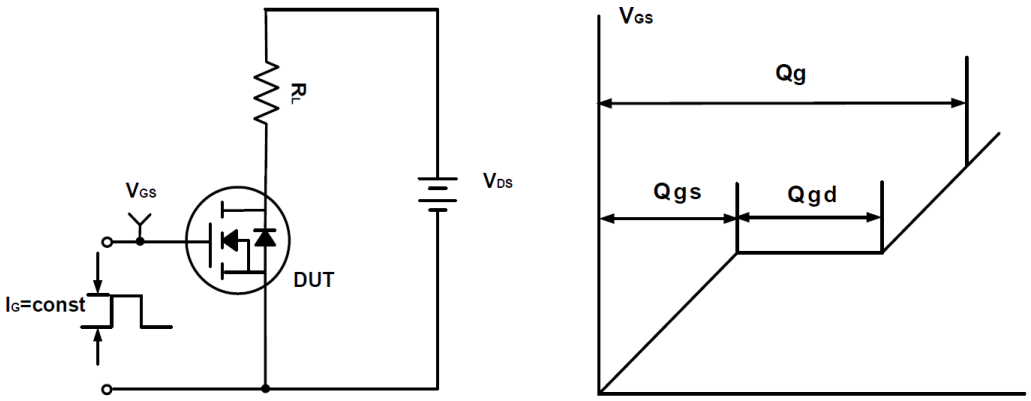

Figure A Gate Charge Test Circuit &Waveforms

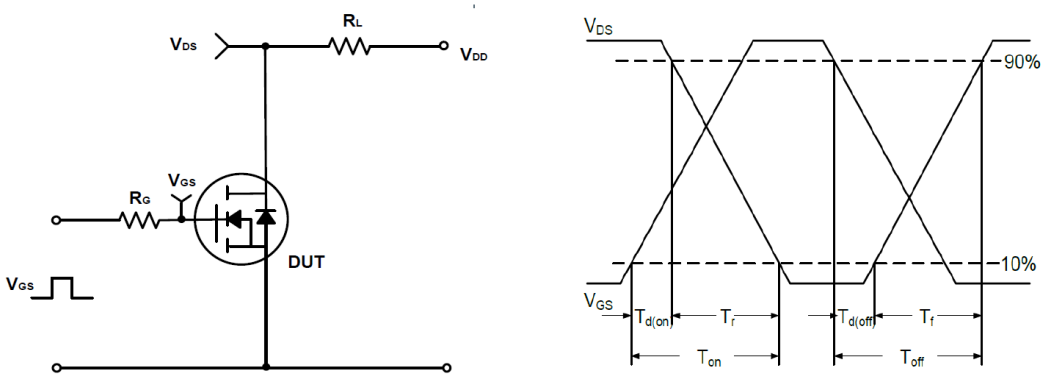

Figure B Switching Test Circuit & Waveforms

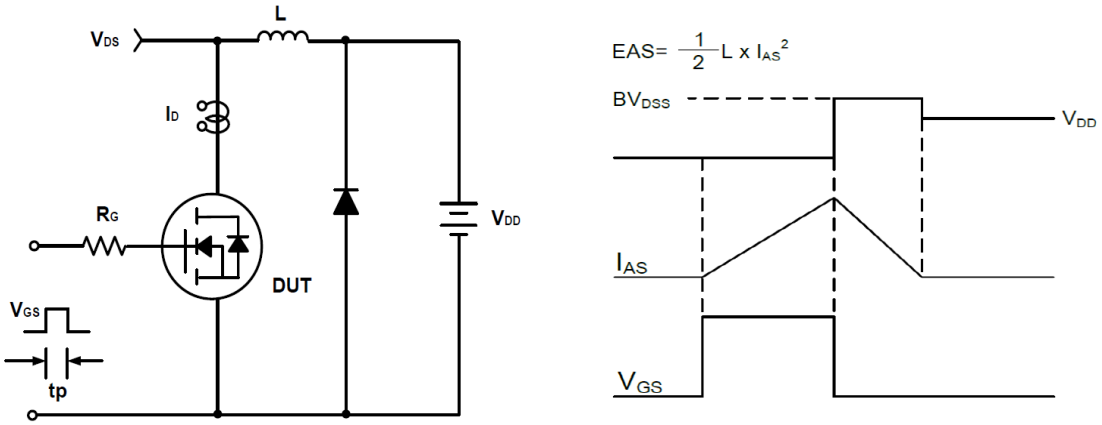

Figure C Unclamped Inductive Switching Circuit & Waveforms

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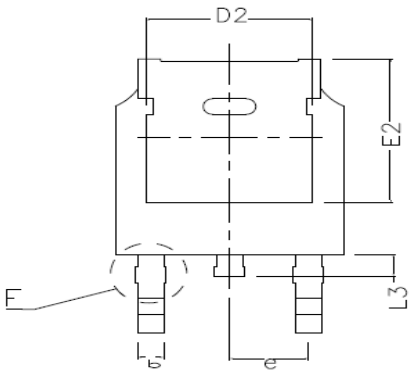
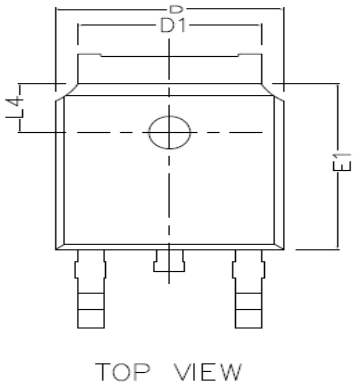
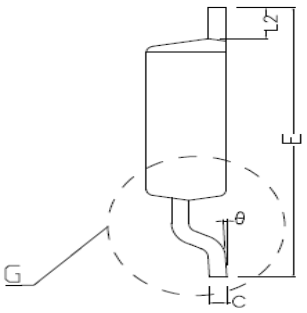
TO-252 Package Outline Dimensions (Units: mm)



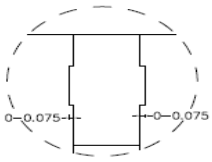
BOTTOM VIEW



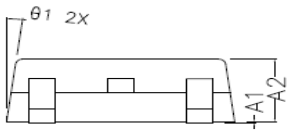
TOP VIEW



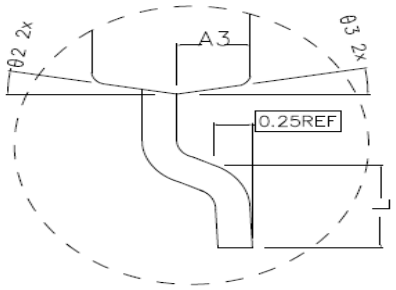
SIDE VIEW



DETAIL F



SIDE VIEW



DETAIL G

COMMON DIMENSIONS (UNITS OF MEASURE IS mm)			
	MIN	NORMAL	MAX
A1	0.000	0.100	0.150
A2	2.200	2.300	2.400
A3	1.020	1.070	1.120
b	0.710	0.760	0.810
c	0.460	0.508	0.550
D	6.500	6.600	6.700
D1		5.330REF	
D2		4.830REF	
E	9.900	10.100	10.300
E1	6.000	6.100	6.200
E2		5.600REF	
e		2.286TYPE	
L	1.400	1.550	1.700
L2		1.10REF	
L3		0.80REF	
L4		1.80REF	
θ		0~8°	
θ1		7° TYPE	
θ2		10° TYPE	
θ3		10° TYPE	